

TRANSISTOR (PNP)
Plastic-Encapsulate Transistor
FEATURES

Power dissipation

P_{CM} : 0.9W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : -2A

Collector-base voltage

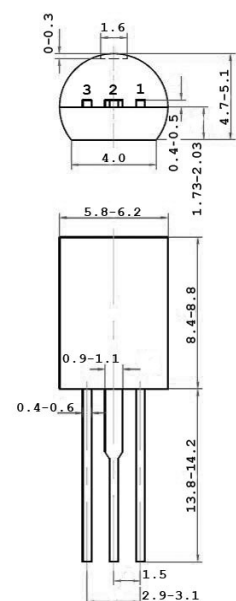
$V_{(BR)CBO}$: -20V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

TO-92MOD

1. EMITTER
2. COLLECTOR
3. BASE



UNIT:mm

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at $25^{\circ}C$ ambient temperature unless otherwise specified.

ELECTRICAL CHARACTERISTICS

Parameters	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=-1mA, I_E=0$	-20			V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=-10mA, I_B=0$	-10			V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=-1mA, I_C=0$	-6			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-20V, I_E=0$			-0.1	μA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=-6V, I_C=0$			-0.1	μA
DC Current Gain	$h_{FE(1)}$ $h_{FE(2)}$	$V_{CE}=-1V, I_C=-0.5A$ $V_{CE}=-1V, I_C=-4A$	140 60		600	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-2A, I_B=-50mA$		-0.2	-0.5	V
Base-Emitter Voltage	$V_{BE(on)}$	$V_{CE}=-1V, I_C=-2A$			-1.5	V
Transition Frequency	f_T	$V_{CE}=-1V, I_C=-0.5A$		140		MHz
Output Capacitance	C_{ob}	$V_{CE}=-10V, I_E=0, f=1MHz$		50		pF

CLASSIFICATION OF h_{FE}

Rank	A	B	C
Range	140-280	200-400	300-600